



## Electrostatic Discharge (ESD) Testing Report

Applicant Department: MingXin Microelectronics Corporation LTD	
Product: MX308SE	Case NO: S121127006
Test Item: System-Level ESD Testing	Package Pin Count: SOP8
Application Date: 11/27/2012	Date Finished: 11/27/2012
Test Method: IEC 61000-4-2(150pF/330ohm) & (100pF/1500ohm)	
Test Equipment: EMI TEST / ESD P30C	Temperature: 25°C ± 5°C Humidity: 55% ± 10% RH
Failure Criteria: Device no longer meets the static driving requirements using V+I envelope around REFERENCE I-V curve (pre-zap). (Current tolerance ± 30%, Voltage tolerance ± 30%)	
Test Voltage: (±)8KV, (±)15KV	

## ESD GUN TESTING Result

MODEL: ESD GUN	ESD SENSITIVITY PASS +/-1500V		
TEST MODE ZAP VOLTAGE	SAMPLE SIZE	PASSED VOLTS	
Contact Discharge (Zap +/-8000V)	Condition 1* 150pF/330ohm	3(#7,#8,#9)	+/-8000V
Air Discharge (Zap +/-15000V)		3(#10,#11,#12)	+/-15000V
Contact Discharge (Zap +/-8000V)	Condition 2* 150pF/330ohm	3(#13,#14,#15)	+/-8000V
Air Discharge (Zap +/-15000V)		3(#16,#17,#18)	+/-15000V
Contact Discharge (Zap +/-8000V)	Condition 3* 150pF/330ohm	3(#19,#20,#21)	+/-8000V
Air Discharge (Zap +/-15000V)		3(#22,#23,#24)	+/-15000V
Contact Discharge (Zap +/-8000V)	Condition 4* 150pF/330ohm	3(#25,#26,#27)	+/-8000V
Air Discharge (Zap +/-15000V)		3(#28,#29,#30)	+/-15000V
Contact Discharge (Zap +/-15000V)	Condition 5* 100pF/1500ohm	3(#38,#39,#40)	+/-15000V



## Electrostatic Discharge (ESD) Testing Report

Applicant/Department: MingXin Microelectronics Corporation LTD	
Product: MX3085E	Case NO: S121127006
Test Item: Human Body Model (HBM)	Package/Pin Count: SOP8
Application Date: 11/27/2012	Date Finished: 11/27/2012
Test Method: MIL-STD-883H Method 3015.8	Zap: 3 pulse, Interval: 1.0 S
Test Equipment: Themo Keytek Zapmaster7/4 tester	Temperature: 25°C±5°C Humidity: 55%RH±10%RH
Failure Criteria: Device no longer meets the parts drawing requirements using V+I envelope around REFERENCE I-V curve (pre-zap). (Current tolerance ± 30%, Voltage tolerance ± 30 %)	
Test Voltage: 2000V(+/-); 4000V(+/-)	

## HUMAN-BODY MODEL TESTING Result

MODEL: HBM	ESD SENSITIVITY PASS: <u>+/-4000V</u>		V CLASS: CLASS 3A
PIN COMBINATION	SAMPLE SIZE	PASSED VOLTS	NOTE:
All other pins to GND(+/-) IO pins to VCC(+/-) IO pins to IO pins (+/-)	2000V 3	+/-2000V	FOR MIL-STD-883H Method 3015.8 CLASS 0 : <250V CLASS 1A: 250V < 500V CLASS 1B: 500V <1000V CLASS 1C: 1000V <2000V CLASS 2 : 2000V <4000V CLASS 3A : 4000V < 8000V CLASS 3B : 8000V~
All other pins to GND(+/-) IO pins to VCC(+/-) IO pins to IO pins (+/-)	4000V 3	+/-4000V	

## Pin Assignment

GND: 5  
VCC: 8  
IO: Other Pins

## Remark:

This report refers only to the specimen submitted to testing, and be invalid as separately used.

Testing Engineer:	Approved by:
Waiting Wang	Sharma



All other pins to GND(+/-)

IO pins to VCC(+/-)

IO pins to IO pins (+/-)

2000V

(Unit:V)

Test Pin Fail Voltage	#1	#2	#3	Test Pin Fail Voltage	#1	#2	#3
1	PASS	PASS	PASS	6	PASS	PASS	PASS
2	PASS	PASS	PASS	7	PASS	PASS	PASS
3	PASS	PASS	PASS	8	PASS	PASS	PASS
4	PASS	PASS	PASS				

All other pins to GND(+/-)

IO pins to VCC(+/-)

IO pins to IO pins (+/-)

4000V

(Unit:V)

Test Pin Fail Voltage	#4	#5	#6	Test Pin Fail Voltage	#4	#5	#6
1	PASS	PASS	PASS	6	PASS	PASS	PASS
2	PASS	PASS	PASS	7	PASS	PASS	PASS
3	PASS	PASS	PASS	8	PASS	PASS	PASS
4	PASS	PASS	PASS				